



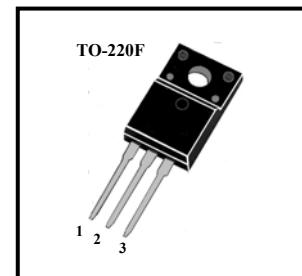
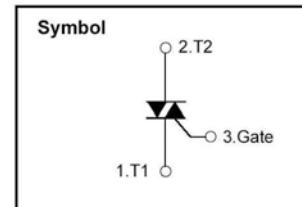
Shantou Huashan Electronic Devices Co.,Ltd.

HTF6A60

INSULATED TYPE TRIAC (TO-220F PACKAGE)

■ Features

- * Repetitive Peak Off-State Voltage: 600V
- * R.M.S On-State Current($I_{T(RMS)}=6A$)
- * High Commutation dv/dt
- * Isolation Voltage ($V_{ISO}=1500V$ AC)



■ General Description

This device is fully isolated package suitable for AC switching application, phase control application such as fan speed and temperature modulation control, lighting control and static switching relay.

■ Absolute Maximum Ratings ($T_a=25^\circ C$)

| | | |
|---|-------|-----------|
| T_{stg} — Storage Temperature | | -40~150°C |
| T_j — Operating Junction Temperature | | -40~125°C |
| P_{GM} — Peak Gate Power Dissipation | | 5W |
| V_{DRM} — Repetitive Peak Off-State Voltage | | 600V |
| I_T (RMS) — R.M.S On-State Current ($T_c=94^\circ C$) | | 6A |
| V_{GM} — Peak Gate Voltage | | 10V |
| I_{GM} — Peak Gate Current | | 2.0A |
| I_{TSM} — Surge On-State Current (One Cycle, 50/60Hz,Peak,Non-Repetitive) | | 60/66A |
| V_{ISO} — Isolation Breakdown Voltage (R.M.S, A.C.1minute) | | 1500V |

■ Electrical Characteristics ($T_a=25^\circ C$)

| Symbol | Items | Min | | Max | Unit | Conditions |
|---------------|---|-----|----|-----|------------|--|
| I_{DRM} | Repetitive Peak Off-State Current | | | 1.0 | mA | $V_D=V_{DRM}$, Single Phase, Half Wave, $T_j=125^\circ C$ |
| V_{TM} | Peak On-State Voltage | | | 1.5 | V | $I_T=8A$, Inst. Measurement |
| I^{+}_{GT1} | Gate Trigger Current (I) | | | 20 | mA | $V_D=6V$, $R_L=10$ ohm |
| I^{-}_{GT1} | Gate Trigger Current (II) | | | 20 | mA | $V_D=6V$, $R_L=10$ ohm |
| I^{-}_{GT3} | Gate Trigger Current (III) | | | 20 | mA | $V_D=6V$, $R_L=10$ ohm |
| V^{+}_{GT1} | Gate Trigger Voltage (I) | | | 1.5 | V | $V_D=6V$, $R_L=10$ ohm |
| V^{-}_{GT1} | Gate Trigger Voltage (II) | | | 1.5 | V | $V_D=6V$, $R_L=10$ ohm |
| V^{-}_{GT3} | Gate Trigger Voltage (III) | | | 1.5 | V | $V_D=6V$, $R_L=10$ ohm |
| V_{GD} | Non-Trigger Gate Voltage | 0.2 | | | V | $T_j=125^\circ C$, $V_D=1/2V_{DRM}$ |
| $(dv/dt)_c$ | Critical Rate of Rise of Off-State Voltage at Commutation | 5.0 | | | V/ μ s | $T_j=125^\circ C$, $V_D=2/3V_{DRM}$ $(di/dt)_c=-3A/ms$ |
| I_H | Holding Current | | 10 | | mA | |
| $R_{th(j-c)}$ | Thermal Resistance | | | 3.8 | °C/W | Junction to case |



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■ Performance Curves

Fig 1. Gate Characteristics

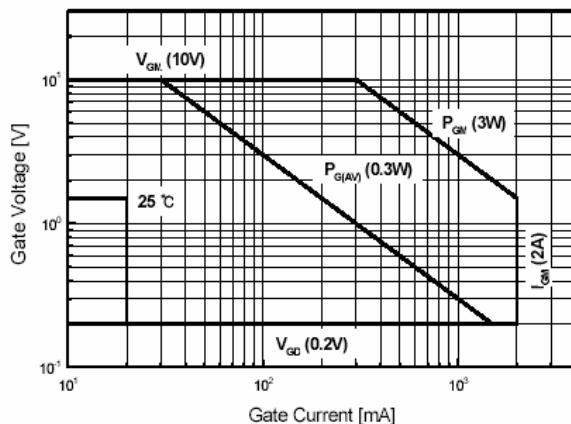


Fig 2. On-State Voltage

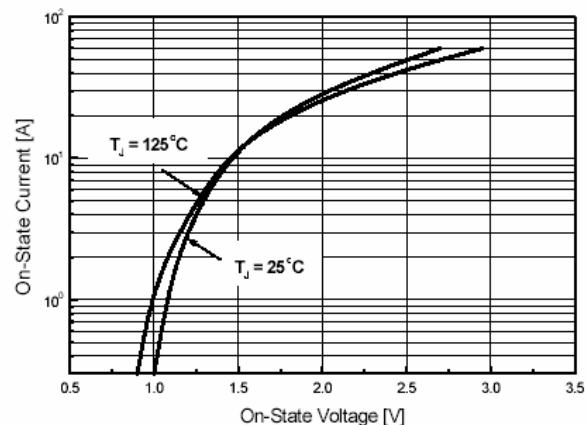


Fig 3. On State Current vs.
Maximum Power Dissipation

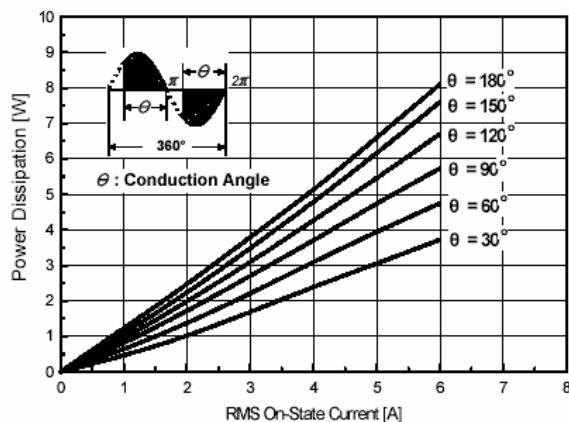


Fig 4. On State Current vs.
Allowable Case Temperature

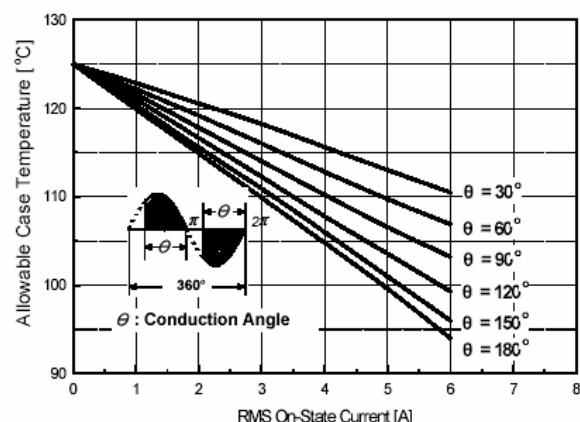


Fig 5. Surge On-State Current Rating
(Non-Repetitive)

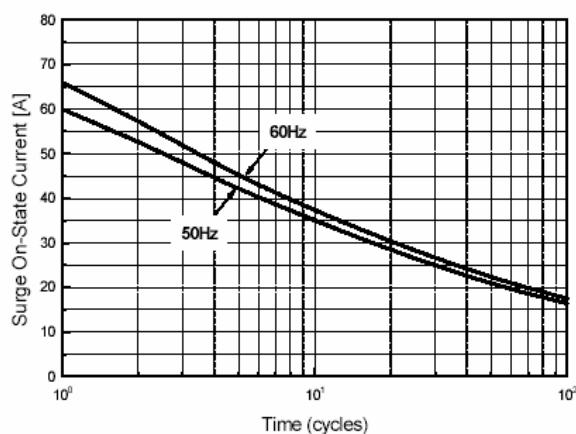
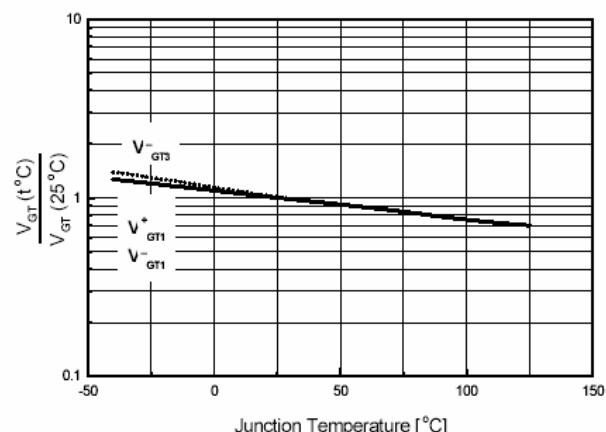


Fig 6. Gate Trigger Voltage vs.
Junction Temperature





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Fig 7. Gate Trigger Current vs.
Junction Temperature

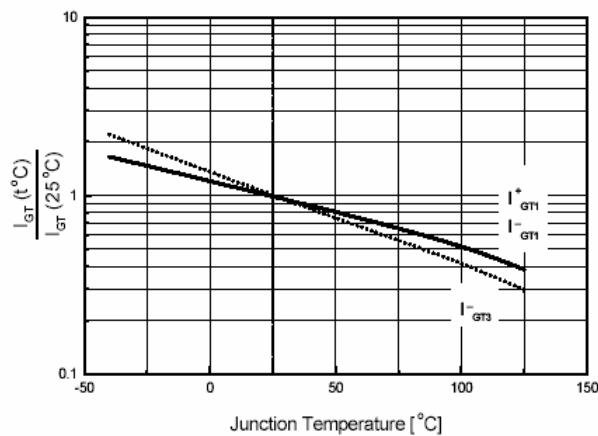


Fig 8. Transient Thermal Impedance

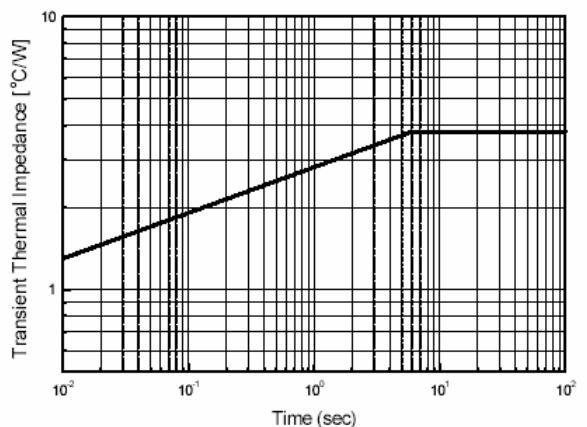


Fig 9. Gate Trigger Characteristics Test Circuit

